

SLA6020

NPN Silicon Triple Diffused Planar Darlington
PNP Silicon Epitaxial Planar Darlington

Absolute maximum ratings

(Ta=25°C)

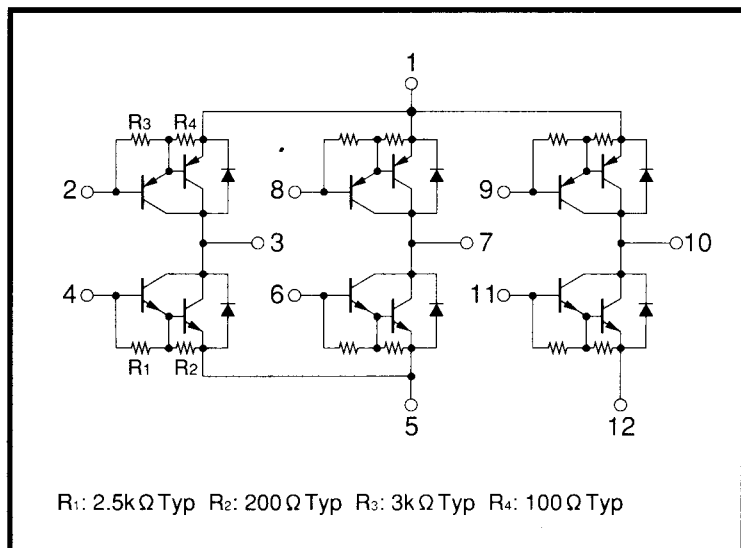
Parameter	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CBO}	100	−100	V
Collector-Emitter Voltage	V _{CEO}	100	−100	V
Emitter-Base Voltage	V _{EB0}	6	−6	V
Collector Current	I _c	5	−5	A
Collector Current	I _{CP}	8 (P _w ≤1ms, D _u ≤50%)		A
Base Current	I _B	0.5	−0.5	A
Total Power Dissipation	P _T	5 (T _a =25℃)		W
		25 (T _c =25℃)		
Isolation Voltage	V _{ISO}	1000 (Between fin and lead pin, AC)		V _{rms}
Storage Temperature	T _{stg}	−40 to +150		℃
Thermal Resistance	θ _{J-C}	5		℃/W

Electrical characteristics

(Ta=25°C)

Parameter	Symbol	NPN	PNP
Collector Cut-off Current	I _{CBO}	10 μA max (V _{CB} =100V)	-10 μA max (V _{CB} =-100V)
Emitter Cut-off Current	I _{EBO}	10mA max (V _{EB} =6V)	-10mA max (V _{EB} =-6V)
Collector-Emitter Voltage	V _{CEO}	100V min (I _c =10mA)	-100V min (I _c =-10mA)
DC Current Gain	h _{FE}	2000min (V _{CE} =4V, I _c =3A)	2000min (V _{CE} =-4V, I _c =-3A)
Collector-Emitter Saturation Voltage	V _{CE(sat)}	1.5V max (I _c =3A, I _B =6mA)	-1.5V max (I _c =-3A, I _B =-6mA)

Equivalent circuit diagram



External dimensions (Unit: mm)

